

## WBP8-5

### Study on $(\text{Nd}_x\text{Sr}_{1-x})\text{TiO}_3$ thin film as conductive buffer layer for low-cost REBCO wire

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To develop low-cost REBCO superconducting wires, we have developed a new architecture using conductive rather than insulating buffer layers, combined with  $\{100\}\langle 001\rangle$  textured pure Cu tape to form  $\text{YBa}_2\text{Cu}_3\text{O}_7/\text{Nb}$ -doped  $\text{SrTiO}_3/\text{Ni}/\text{Cu}/\text{stainless steel}$  tape. In this structure, the textured pure Cu tape is expected to work not only as the template for YBCO biaxial crystal alignment but also as the stabilizing layer. We fabricated  $\text{YBCO}/\text{Sr}(\text{Nb}_{0.15}\text{Ti}_{0.85})\text{O}_3/\text{Ni}/\text{Cu}/\text{SUS316}$  short sample with the  $J_c$  of  $2.5 \text{ MA}/\text{cm}^2$  (at 77 K, self-field), and also confirmed that some current flowed into the Cu tape through the conductive buffer layers when the current exceeded the critical current of the YBCO layer [1]. However, although the resistivity of  $\text{Sr}(\text{Nb}_{0.15}\text{Ti}_{0.85})\text{O}_3$  was assumed to be approximately  $(1.2\text{--}8.6) \times 10^{-3} \text{ ohm}\cdot\text{cm}$  at 77 K before the YBCO deposition, the resistivity of  $\text{Sr}(\text{Nb}_{0.15}\text{Ti}_{0.85})\text{O}_3$  layer in the  $\text{YBCO}/\text{Sr}(\text{Nb}_{0.15}\text{Ti}_{0.85})\text{O}_3/\text{Ni}/\text{Cu}/\text{SUS316}$  increased to be few  $\text{ohm}\cdot\text{cm}$  after the YBCO deposition and/or oxygen annealing. Because lower resistivity of the conductive buffer layer is favorable, we tried to suppress the increment of the resistivity during the YBCO deposition and oxygen annealing. In this study, we applied  $(\text{Nd}_x\text{Sr}_{1-x})\text{TiO}_3$  to the conductive buffer layer instead of  $\text{Sr}(\text{Nb}_{0.15}\text{Ti}_{0.85})\text{O}_3$ .

The electrical resistivity of the as-grown  $(\text{Nd}_{0.1}\text{Sr}_{0.9})\text{TiO}_3$  thin film prepared on  $\text{LaAlO}_3$  single crystal substrate by a PLD method was  $4.55 \times 10^{-2} \text{ ohm}\cdot\text{cm}$  at 77 K.  $(\text{Nd}_x\text{Sr}_{1-x})\text{TiO}_3$  and YBCO layers were prepared by a PLD method on the Ni-electroplated  $\text{Cu}/\text{SUS316}$  tape. Fig. 1 (a) and (b) show X-ray  $\{110\}$  pole figure and SEM image of the  $(\text{Nd}_{0.1}\text{Sr}_{0.9})\text{TiO}_3$  thin film prepared on the  $\text{Ni}/\text{Cu}/\text{SUS316}$ . We can see that the  $(\text{Nd}_{0.1}\text{Sr}_{0.9})\text{TiO}_3$  film had excellent biaxially crystal orientation and smooth surface. Fig. 1 (c) shows X-ray (102) pole figure of the YBCO prepared on the  $(\text{Nd}_{0.1}\text{Sr}_{0.9})\text{TiO}_3/\text{Ni}/\text{Cu}/\text{SUS316}$ . We confirmed that the YBCO also had excellent biaxially crystal alignment.

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[1] Doi et al., *appl. Phys. Express* 12 (2019) 023010.

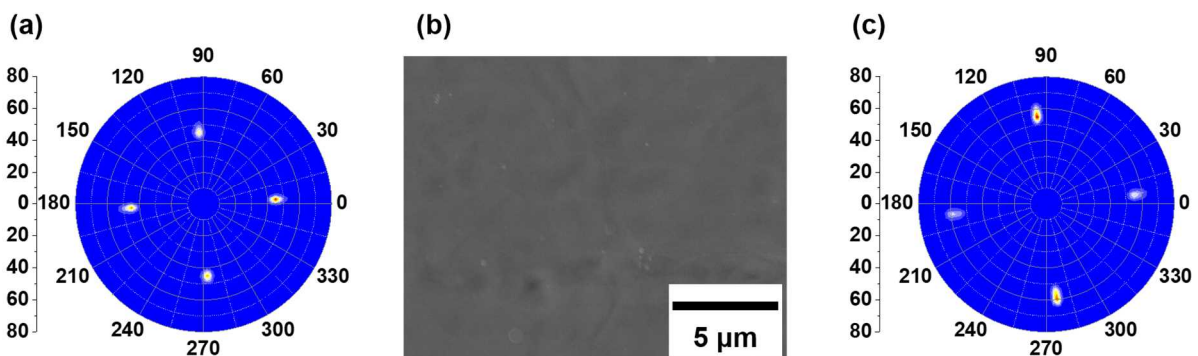


Fig.1(a) X-ray  $\{110\}$  pole figure and (b) SEM image of the  $(\text{Nd}_{0.1}\text{Sr}_{0.9})\text{TiO}_3$  prepared on the  $\text{Ni}/\text{Cu}/\text{SUS}$ , and (c) X-ray (102) pole figure of the YBCO prepared on the  $(\text{Nd}_{0.1}\text{Sr}_{0.9})\text{TiO}_3/\text{Ni}/\text{Cu}/\text{SUS}$ .

Keywords: conductive buffer layer